



# TSC5304D

## High Voltage NPN Transistor with Diode

TO-251



TO-252



Pin assignment:

1. Base
2. Collector
3. Emitter

 $BV_{CEO} = 400V$  $BV_{CBO} = 750V$  $I_C = 4A$  $V_{CE(SAT)} = 1.2V @ I_C / I_B = 4A / 1A$ **Features**

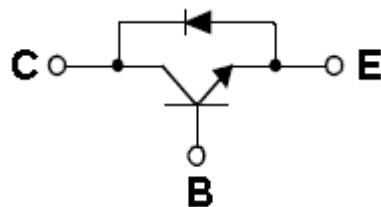
- ◊ Built-in free-wheeling diode makes efficient anti saturation operation.
- ◊ No need to interest an hfe value because of low variable storage-time spread even though come spirit product.
- ◊ Low base drive requirement.
- ◊ Suitable for half bridge light ballast applications.

**Structure**

- ◊ Silicon triple diffused type.
- ◊ NPN silicon transistor with Diode

**Ordering Information**

Part No.	Packing	Package
TSC5304DCH	Tube	TO-251
TSC5304DCP	T&R	TO-252

**Block Diagram****Absolute Maximum Rating** ( $T_a = 25^\circ C$  unless otherwise noted)

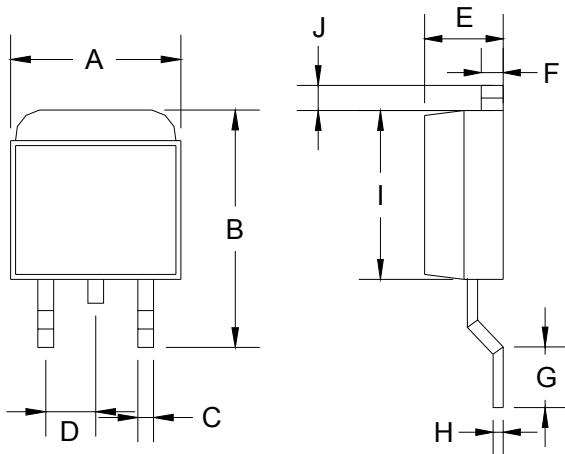
Parameter		Symbol	Limit	Unit
Collector-Base Voltage		$V_{CBO}$	750V	V
Collector-Emitter Voltage		$V_{CEO}$	400V	V
Emitter-Base Voltage		$V_{EBO}$	10	V
Collector Current	DC	$I_C$	4	A
	Pulse		8	
Base Current	DC	$I_B$	1.5	A
	Pulse		4	
Total Power Dissipation ( $T_c=25^\circ C$ )		$P_D$	35	W
Operating Junction Temperature		$T_J$	+150	$^\circ C$
Operating Junction and Storage Temperature Range		$T_{STG}$	-65 to +150	$^\circ C$
Thermal Resistance Junction to Case		$R_{\theta jc}$	6	$^\circ C/W$
Thermal Resistance Junction to Ambient		$R_{\theta ja}$	90	$^\circ C/W$

Note: 1. Single pulse,  $P_w = 300\mu S$ , Duty  $\leq 2\%$

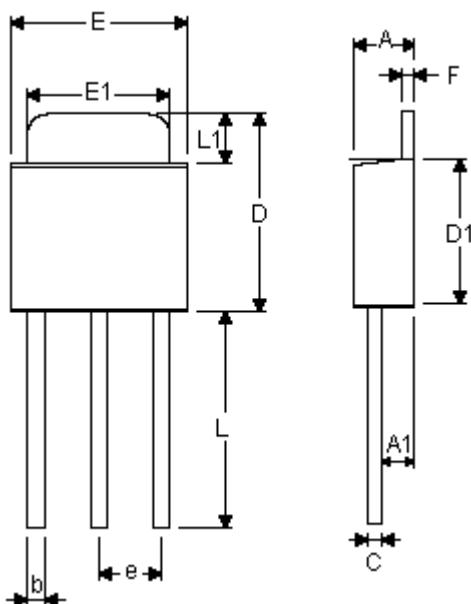
## Electrical Characteristics

Parameter	Conditions	Symbol	Min	Typ	Max	Unit
<b>Static</b>						
Collector-Base Voltage	$I_C = 1\text{mA}$ , $I_B = 0$	$BV_{CBO}$	750	--	--	V
Collector-Emitter Breakdown Voltage	$I_C = 5\text{mA}$ , $I_E = 0$	$BV_{CEO}$	400	--	--	V
Emitter-Base Breakdown Voltage	$I_E = 1\text{mA}$ , $I_C = 0$	$BV_{EBO}$	9	--	--	V
Collector Cutoff Current	$V_{CB} = 500\text{V}$ , $I_E = 0$	$I_{CBO}$	--	--	10	uA
Emitter Cutoff Current	$V_{EB} = 9\text{V}$ , $I_C = 0$	$I_{EBO}$	--	--	10	uA
Collector-Emitter Saturation Voltage	$I_C / I_B = 1.0\text{A} / 0.2\text{A}$	$V_{CE(SAT)}1$	--	--	0.35	V
	$I_C / I_B = 2.0\text{A} / 0.5\text{A}$	$V_{CE(SAT)}2$	--	--	0.55	
	$I_C / I_B = 4.0\text{A} / 1.0\text{A}$	$V_{CE(SAT)}3$	--	--	1.25	
Base-Emitter Saturation Voltage	$I_C / I_B = 1.0\text{A} / 0.2\text{A}$	$V_{CB(SAT)}1$	--	--	1.0	V
	$I_C / I_B = 2.0\text{A} / 0.5\text{A}$	$V_{CB(SAT)}2$	--	--	1.1	
DC Current Gain	$V_{CE} = 5\text{V}$ , $I_C = 0.5\text{A}$	$h_{FE} 1$	15	20	--	
	$V_{CE} = 5\text{V}$ , $I_C = 2\text{A}$	$h_{FE} 2$	10	--	--	
Turn On Time	$V_{CC} = 250\text{V}$ , $I_C = 2\text{A}$ , $I_{B1} = I_{B2} = 0.4\text{A}$ , $t_p = 25\mu\text{s}$	$t_{ON}$	--	--	0.5	uS
Storage Time		$t_{STG}$	--	--	3	uS
Fall Time		$t_F$	--	--	0.2	uS
<b>Diode</b>						
Fall Time	$I_C = 2\text{A}$	$t_F$	--	--	500	nS
Forward Voltage	$I_C = 2\text{A}$	$V_f$	--	--	1.3	V

Note : pulse test: pulse width <=300uS, duty cycle <=2%

TO-252 Mechanical Drawing

TO-252 DIMENSION				
DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	6.570	6.840	0.259	0.269
B	9.250	10.400	0.364	0.409
C	0.550	0.700	0.022	0.028
D	2.560	2.670	0.101	0.105
E	2.300	2.390	0.090	0.094
F	0.490	0.570	0.019	0.022
G	1.460	1.580	0.057	0.062
H	0.520	0.570	0.020	0.022
I	5.340	5.550	0.210	0.219
J	1.460	1.640	0.057	0.065

TO-251 Mechanical Drawing

TO-251 DIMENSION				
DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	2.20	2.4	0.087	0.095
A1	1.10	1.30	0.043	0.051
b	0.40	0.80	0.016	0.032
C	0.40	0.60	0.016	0.024
D	6.70	7.30	0.264	0.287
D1	5.40	5.65	0.213	0.222
E	6.40	6.65	0.252	0.262
e	2.10	2.50	0.083	0.098
F	0.40	0.60	0.016	0.024
L	7.00	8.00	0.276	0.315
L1	1.60	1.86	0.063	0.073